ON Semiconductor®

FDMC0202S

N-Channel Power Trench® SyncFET™
25 V, 40 A, 3.15 mΩ

Features

- Max $r_{DS(on)}$ = 3.15 mΩ at V_{GS} = 10 V, I_D = 22.5 A
- Max $r_{DS(on)}$ = 4.7 mΩ at V_{GS} = 4.5 V, I_D = 18 A
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- SyncFET Schottky Body Diode
- 100% UIL Tested
- RoHS Compliant

General Description

The FDMC0202S has been designed to minimize losses in power conversion application. Advancements in both silicon and package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance. This device has the added benefit of an efficient monolithic Schottky body diode.
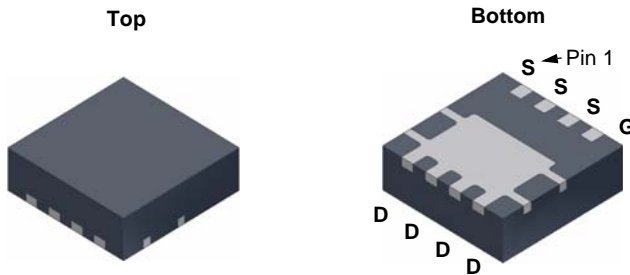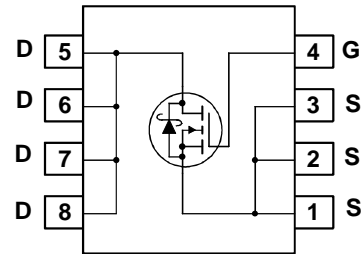
Applications

- Synchronous Rectifier for DC/DC Converters
- Notebook Vcore/ GPU low side switch
- Networking Point of Load low side switch
- Telecom secondary side rectification

Top　　　**Bottom**

Power 33

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			25	V
V_{GS}	Gate to Source Voltage		(Note 4)	±20	V
I_D	Drain Current -Continuous (Package limited)	T_C = 25 °C		40	A
	-Continuous (Silicon limited)	T_C = 25 °C		103	
	-Continuous	T_A = 25 °C	(Note 1a)	22.5	
	-Pulsed			120	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	84	mJ
P_D	Power Dissipation	T_C = 25 °C		52	W
	Power Dissipation	T_A = 25 °C	(Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC0202S	FDMC0202S	Power 33	13 ''	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0 V	25			V
$\dfrac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 10 mA, referenced to 25 °C		21		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 20 V, V_{GS} = 0 V			500	µA
I_{GSS}	Gate to Source Leakage Current, Forward	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 1 mA	1.2	1.7	3.0	V
$\dfrac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 10 mA, referenced to 25 °C		-5		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 22.5 A		2.5	3.15	mΩ
		V_{GS} = 4.5 V, I_D = 18 A		3.6	4.7	
		V_{GS} = 10 V, I_D = 22.5 A, T_J = 125 °C		3.5	4.5	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 22.5 A		122		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 13 V, V_{GS} = 0 V, f = 1 MHz		2031	2705	pF
C_{oss}	Output Capacitance			596	795	pF
C_{rss}	Reverse Transfer Capacitance			134	205	pF
R_g	Gate Resistance			1.1	2.4	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 13 V, I_D = 22.5 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		11	22	ns
t_r	Rise Time			3.6	10	ns
$t_{d(off)}$	Turn-Off Delay Time			26	41	ns
t_f	Fall Time			3	10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V		31	44	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 4.5 V, V_{DD} = 13 V, I_D = 22.5 A		14	20	nC
Q_{gs}	Gate to Source Gate Charge			6.5		nC
Q_{gd}	Gate to Drain "Miller" Charge			3.9		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 22.5 A (Note 2)		0.79	1.2	V
		V_{GS} = 0 V, I_S = 2 A (Note 2)		0.47	0.8	
t_{rr}	Reverse Recovery Time	I_F = 22.5 A, di/dt = 300 A/µs		24	39	ns
Q_{rr}	Reverse Recovery Charge			19	34	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
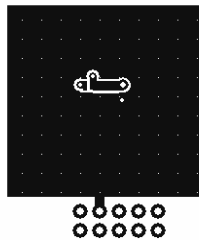
53 °C/W when mounted on a 1 in^2 pad of 2 oz copper
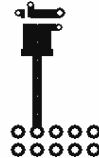
125 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 µs, Duty cycle < 2.0 %.

3. E_{AS} of 84 mJ is based on starting T_J = 25 °C, L = 1 mH, I_{AS} = 13 A, V_{DD} = 23 V, V_{GS} = 10 V. 100% test at L = 0.3 mH, I_{AS} = 20 A.

4. As an N-ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

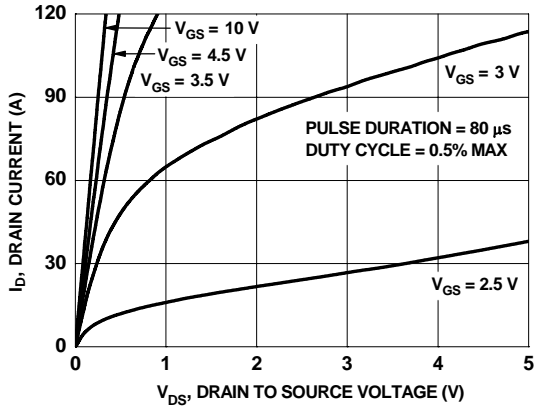**Typical Characteristics** T_J = 25 °C unless otherwise noted

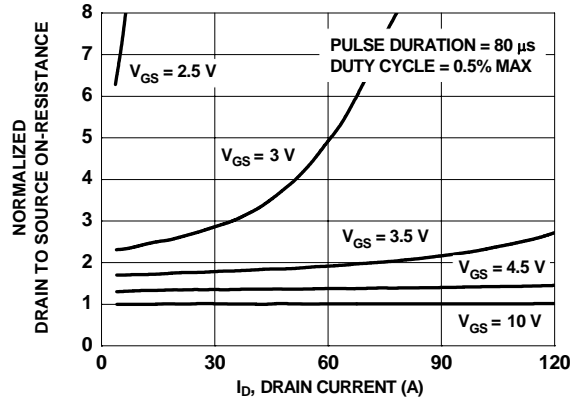Figure 1. On-Region Characteristics

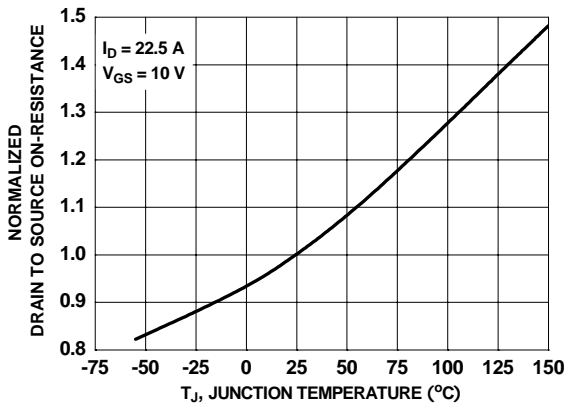Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

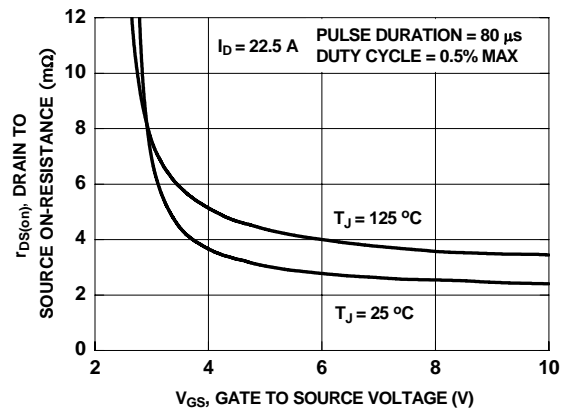Figure 3. Normalized On-Resistance vs Junction Temperature

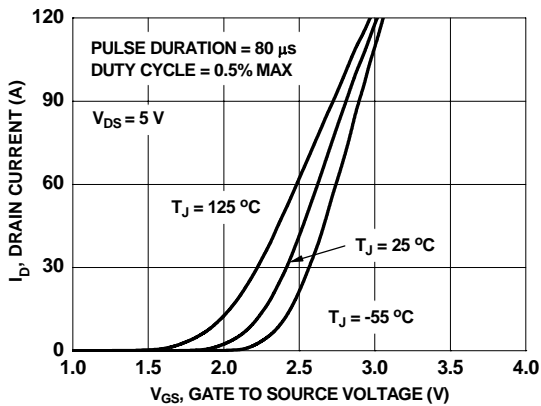Figure 4. On-Resistance vs Gate to Source Voltage
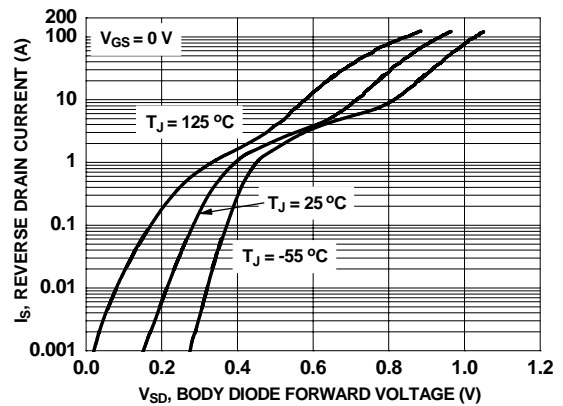

Figure 5. Transfer Characteristics

Figure 6. Source to Drain Diode Forward Voltage vs Source Current

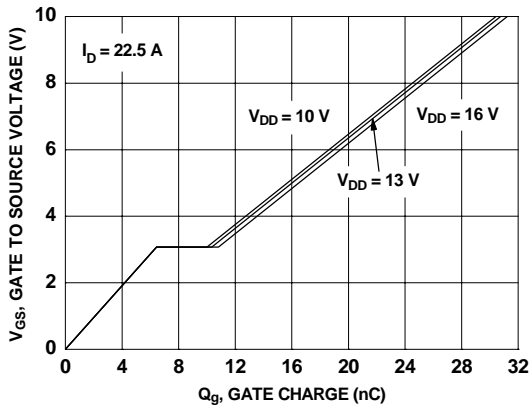**Typical Characteristics** T_J = 25 °C unless otherwise noted

Figure 7. Gate Charge Characteristics
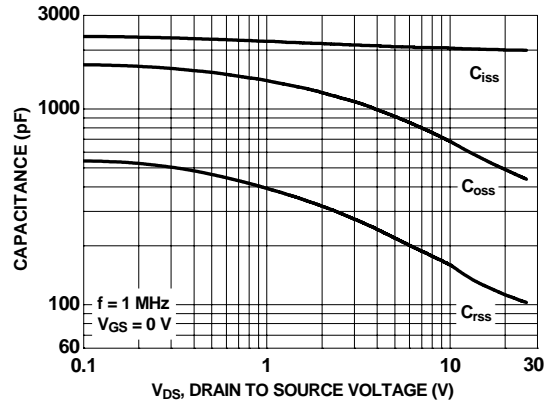
Figure 8. Capacitance vs Drain to Source Voltage
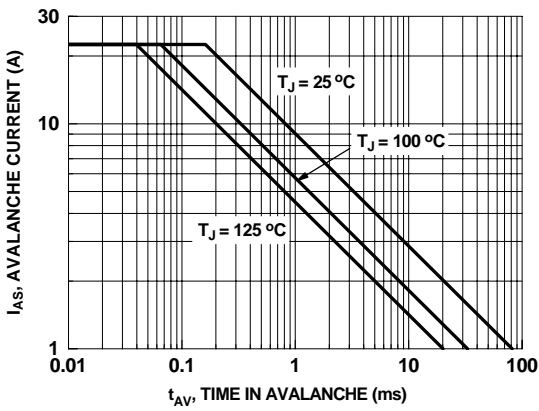
Figure 9. Unclamped Inductive Switching Capability
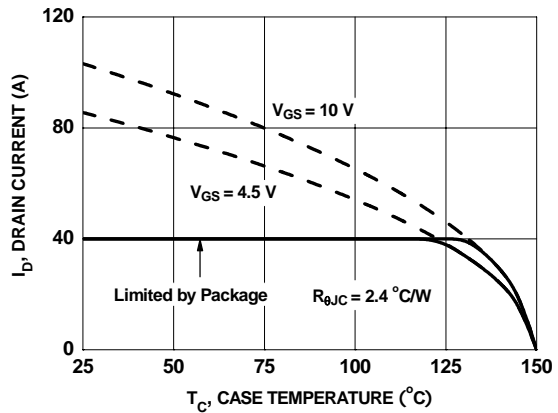
Figure 10. Maximum Continuous Drain Current vs Case Temperature
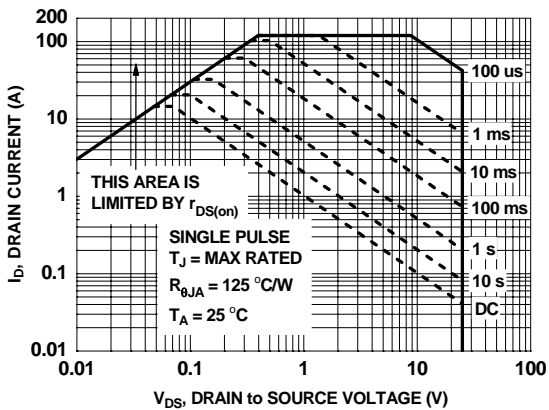
Figure 11. Forward Bias Safe Operating Area
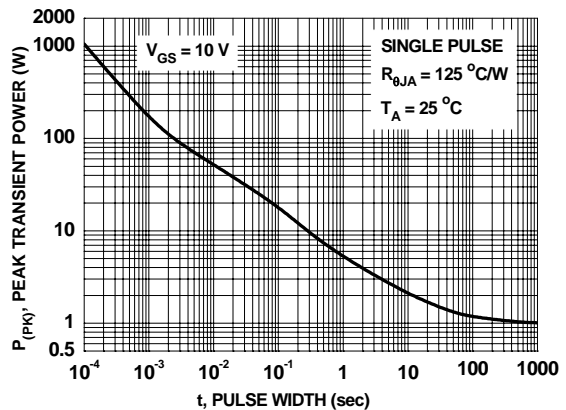
Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted
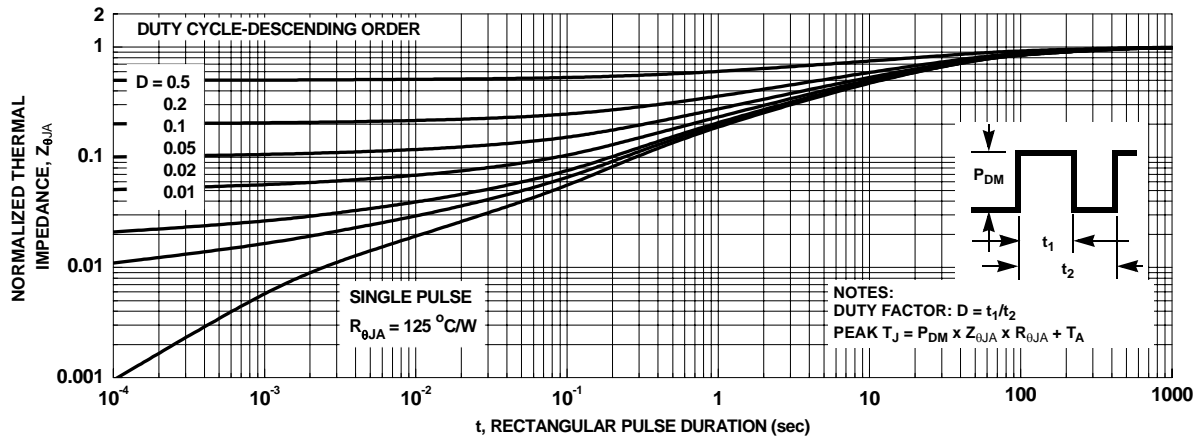
Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET Schottky body diode Characteristics

ON Semiconductor SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 13 shows the reverses recovery characteristic of the FDMC0202S.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.
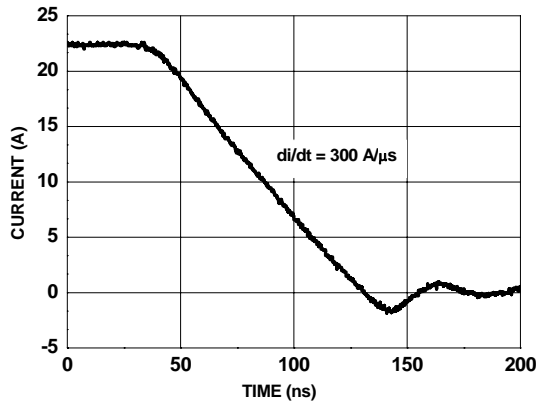
Figure 13. FDMC0202S SyncFET body diode reverse recovery characteristic
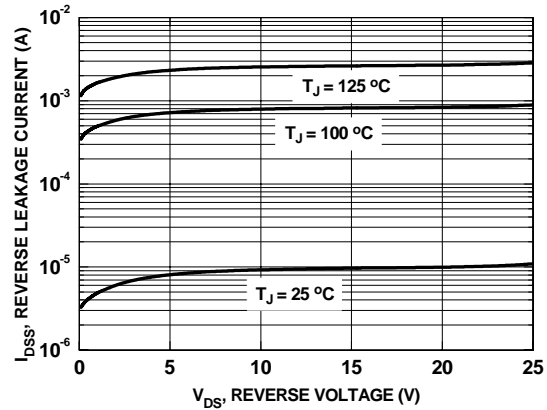
Figure 14. SyncFET body diode reverses leakage versus drain-source voltage

Dimensional Outline and Pad Layout

3.30±0.10 A

PKG ℄

8   5

PKG ℄   3.30±0.10

1   4

SEE
DETAIL A

2.37 MIN

SYM ℄

8   5

(0.45)

(0.40)   2.15 MIN

PKG ℄

(0.65)

0.70 MIN

1   4

0.65   0.42 MIN

1.95
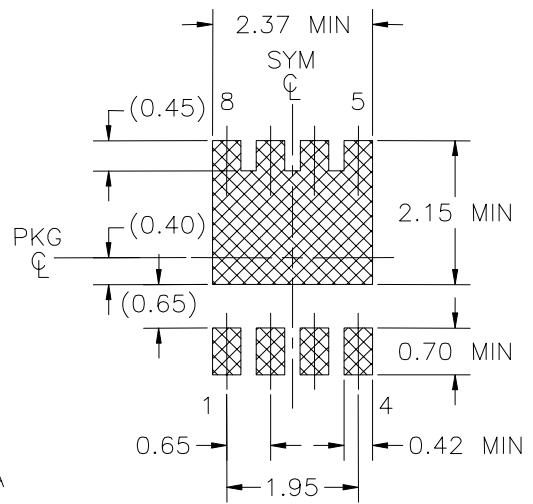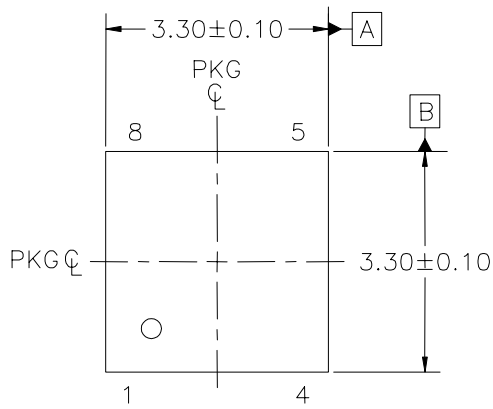
LAND PATTERN
RECOMMENDATION

1.95

0.32±0.05   0.65

⊕ 0.10 C A B

1   4

0.40±0.10

(0.20)

PKG ℄

2.00±0.10

(0.39)   8   5

(2.27)

(0.52)

// 0.10 C

1.10
0.90

⌓ 0.08 C

0.05
0.00

0.20±0.025

SEATING
PLANE

C

DETAIL A
SCALE: 2X
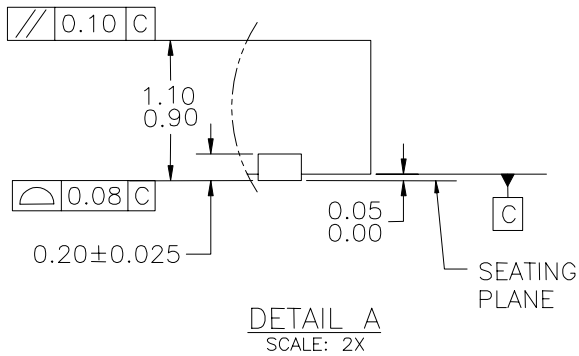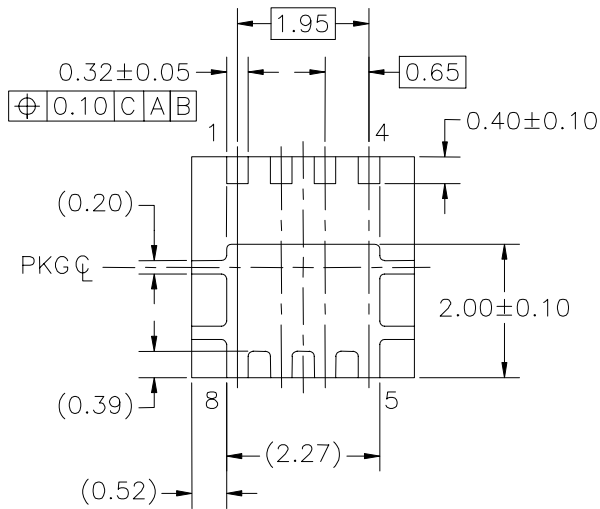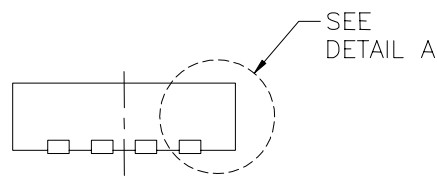
NOTES: UNLESS OTHERWISE SPECIFIED

A) PACKAGE STANDARD REFERENCE:
   JEDEC MO−240, ISSUE A, VAR. BA,
   DATED OCTOBER 2002.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE BURRS
   OR MOLD FLASH. MOLD FLASH OR
   BURRS DOES NOT EXCEED 0.10MM.
D) DIMENSIONING AND TOLERANCING PER
   ASME Y14.5M−1994.
E) DRAWING FILE NAME: PQFN08BREV1

PQFN08BREV1

PUBLICATION ORDERING INFORMATION

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